Dual 4-input multiplexer; 3-state Rev. 03 — 22 April 2010

Product data sheet

#### **General description** 1.

The 74HC253; 74HCT253 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC253; 74HCT253 provides a dual 4-input multiplexer with 3-state outputs which selects 2 bits of data from up to four sources selected by common data select inputs (S0, S1). The two 4-input multiplexer circuits have individual active LOW output enable inputs  $(1\overline{OE}, 2\overline{OE}).$ 

The 74HC253 and 74HCT253 are the logic implementation of a 2-pole, 4-position switch, where the position of the switch is determined by the logic levels applied to S0 and S1. The outputs are forced to a high-impedance OFF-state when  $n\overline{OE}$  is HIGH.

The logic equations for the outputs are:

 $1Y = 1\overline{OE} \bullet (110 \bullet \overline{S1} \bullet \overline{S0} + 111 \bullet \overline{S1} \bullet S0 + 112 \bullet S1 \bullet \overline{S0} + 113 \bullet S1 \bullet S0)$  $2Y = 2\overline{OE} \bullet (2I0 \bullet \overline{S1} \bullet \overline{S0} + 2I1 \bullet \overline{S1} \bullet S0 + 2I2 \bullet S1 \bullet \overline{S0} + 2I3 \bullet S1 \bullet S0)$ 

## 2. Features and benefits

- Non-inverting data path
- 3-state outputs interface directly with system bus
- Complies with JEDEC standard no. 7A
- Common select inputs
- Separate output enable inputs
- Input levels:
  - For 74HC253: CMOS level
  - For 74HCT253: TTL level
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C



Dual 4-input multiplexer; 3-state

# 3. Applications

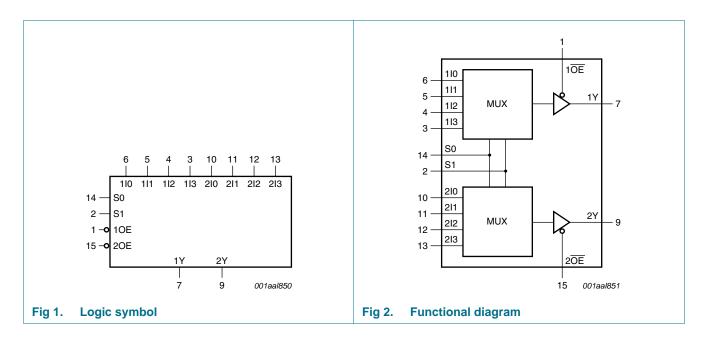
- Data selectors
- Data multiplexers

# 4. Ordering information

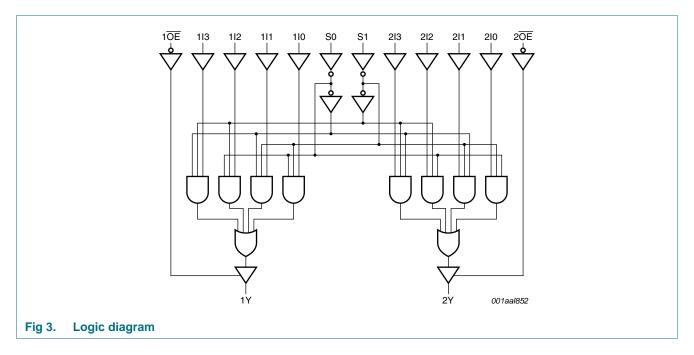
## Table 1.Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC253N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT253N				
74HC253D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width	SOT109-1
74HCT253D			3.9 mm	
74HC253DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads;	SOT338-1
74HCT253DB			body width 5.3 mm	

# 5. Functional diagram

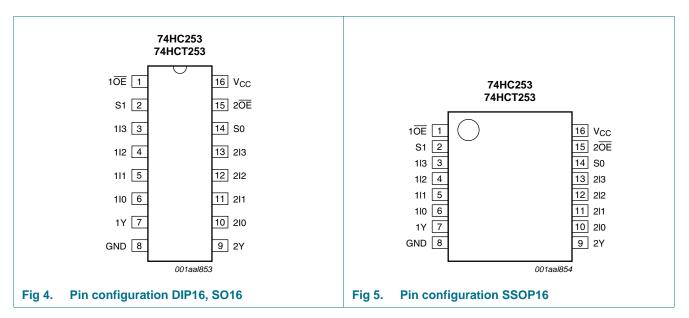


Dual 4-input multiplexer; 3-state



# 6. Pinning information

## 6.1 Pinning



Dual 4-input multiplexer; 3-state

## 6.2 Pin description

cription	
Pin	Description
1, 15	output enable inputs (active LOW)
14, 2	data select inputs
6, 5, 4, 3	data inputs source 1
7	multiplexer output source 1
8	ground (0 V)
9	multiplexer output source 2
10, 11, 12, 13	data inputs source 2
16	supply voltage
	1, 15 14, 2 6, 5, 4, 3 7 8 9 10, 11, 12, 13

# 7. Functional description

### Table 3.Function table<sup>[1]</sup>

select In	puts	data inp	uts			output enable	output
S0	S1	nl0	nl1	nl2	nl3	nOE	nY
Х	x	x	Х	Х	Х	н	Z
L	L	L	Х	Х	Х	L	L
L	L	Н	Х	Х	Х	L	Н
Н	L	Х	L	Х	Х	L	L
Н	L	Х	Н	Х	Х	L	Н
L	Н	Х	Х	L	Х	L	L
L	Н	Х	Х	Н	Х	L	Н
Н	Н	Х	Х	Х	L	L	L
Н	Н	Х	Х	Х	Н	L	Н

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

# 8. Limiting values

### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
Ι <sub>ΟΚ</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±50	mA
I <sub>O</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±35	mA
I <sub>CC</sub>	supply current		-	70	mA
I <sub>GND</sub>	ground current		-70	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C

#### Limiting values ... continued Table 4. In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). Symbol Parameter Conditions Min Max Unit total power dissipation $T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$ Ptot [2] \_ 750 **DIP16** package mW [3] \_ SO16 package 500 mW SSOP16 package [4] \_ 500 mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2]  $~~P_{tot}$  derates linearly with 12 mW/K above 70 °C.

[3] ~~ P\_tot derates linearly with 8 mW/K above 70 °C.

[4] P<sub>tot</sub> derates linearly with 5.5 mW/K above 60 °C.

## 9. Recommended operating conditions

### Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions		74HC253			74HCT253		
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	0	-	$V_{CC}$	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC}$ = 6.0 V	-	-	83	-	-	-	ns/V

## **10. Static characteristics**

### Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbo	I Parameter	Conditions		25 °C		-40 °C to	o +85 °C	–40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC2	53		•							
V <sub>IH</sub>	HIGH-level	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V

## **NXP Semiconductors**

# 74HC253; 74HCT253

Dual 4-input multiplexer; 3-state

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
V <sub>он</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$				I				
	output voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_{O}$ = -20 $\mu$ A; $V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O}$ = 7.8 mA; $V_{CC}$ = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μA
l <sub>oz</sub>	OFF-state output current		-	-	±0.5	-	±5.0	-	±10.0	μA
l <sub>cc</sub>	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	-	80	-	160	μA
CI	input capacitance		-	3.5	-					pF
74HCT2	53									
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>он</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 6.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
1	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
oz	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL}; V_{CC} = 5.5 \text{ V};$ $V_O = V_{CC} \text{ or GND per input}$ pin; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$	-	-	±0.5	-	±5.0	-	±10	μA
l <sub>cc</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	8.0	-	80	-	160	μA

## Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Dual 4-input multiplexer; 3-state

Symbol	Parameter	Conditions		25 °C		–40 °C to +85 °C		–40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
∆I <sub>CC</sub>	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 2.1 \text{ V};\\ \text{other inputs at } V_{CC} \text{ or GND};\\ V_{CC} = 4.5 \text{ V to 5.5 V};\\ I_{O} = 0 \text{ A} \end{array}$	'							'
		per input pin; 1In, 2In inputs	-	40	144	-	180	-	196	μA
		per input pin; nOE input	-	110	396	-	495	-	539	μΑ
		per input pin; Sn input	-	110	396	-	495	-	539	μΑ
CI	input capacitance		-	3.5	-					pF

### Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

# **11. Dynamic characteristics**

### Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); For test circuit see Figure 8.

Symbol	Parameter	Conditions		25	°C	-40 °C to +85 °C	-40 °C to +125 °C	Unit
				Тур	Max	Max	Max	
74HC253	3							
t <sub>pd</sub>	propagation delay	1In to 1Y or 2In to 2Y; see <u>Figure 6</u>	<u>[1]</u>					
		$V_{CC} = 2.0 V$		55	175	220	265	ns
		$V_{CC} = 4.5 V$		20	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		17	-	-	-	ns
		$V_{CC} = 6.0 V$		16	30	37	45	ns
		Sn to nY; see Figure 6						
		$V_{CC} = 2.0 V$		58	175	220	265	ns
		$V_{CC} = 4.5 V$		21	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		18	-	-	-	ns
		$V_{CC} = 6.0 V$		17	30	37	45	ns
t <sub>en</sub>	enable time	nOE to nY; see <u>Figure 7</u>	[2]					
		$V_{CC} = 2.0 V$		30	100	125	150	ns
		$V_{CC} = 4.5 V$		11	20	25	30	ns
		$V_{CC} = 6.0 V$		9	17	21	26	ns
t <sub>dis</sub>	disable time	nOE to nY; see <u>Figure 7</u>	<u>[3]</u>					
		$V_{CC} = 2.0 V$		41	150	190	225	ns
		$V_{CC} = 4.5 V$		15	30	38	45	ns
		$V_{CC} = 6.0 V$		12	26	33	38	ns

Dual 4-input multiplexer; 3-state

Symbol	Parameter	Conditions		25	°C	-40 °C to +85 °C	–40 °C to +125 °C	Unit
			-	Тур	Max	Max	Max	
t <sub>t</sub>	transition time	see Figure 6	[4]					
		$V_{CC} = 2.0 V$		14	60	75	90	ns
		$V_{CC} = 4.5 V$		5	12	15	18	ns
		$V_{CC} = 6.0 V$		4	10	13	15	ns
C <sub>PD</sub>	power dissipation capacitance	per multiplexer; V <sub>I</sub> = GND to $V_{CC}$	<u>[5]</u>	55	-			pF
74HCT25	53							
t <sub>pd</sub>	propagation delay	1In to 1Y or 2In to 2Y; see <u>Figure 6</u>	<u>[1]</u>					
		$V_{CC} = 4.5 V$		20	38	48	57	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		17	-	-		ns
		Sn to nY; see Figure 6						
		$V_{CC} = 4.5 V$		22	40	50	60	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		19	-			ns
t <sub>en</sub>	enable time	n <del>OE</del> to nY; V <sub>CC</sub> = 4.5 V; see Figure 7	[2]	14	30	38	45	ns
t <sub>dis</sub>	disable time	$n\overline{OE}$ to nY; V <sub>CC</sub> = 4.5 V; see <u>Figure 7</u>	<u>[3]</u>	13	30	38	45	ns
t <sub>t</sub>	transition time	$V_{CC}$ = 4.5 V; see <u>Figure 6</u>		5	12	15	18	ns
C <sub>PD</sub>	power dissipation capacitance	per multiplexer; V <sub>I</sub> = GND to V <sub>CC</sub>	<u>[5]</u>	55	-			pF

### Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); For test circuit see <u>Figure 8</u>.

 $\label{eq:tpd} [1] \quad t_{pd} \text{ is the same as } t_{PHL}, \, t_{PLH}.$ 

[2]  $t_{en}$  is the same as  $t_{PZH}$ ,  $t_{PZL}$ .

 $[3] \quad t_{\text{dis}} \text{ is the same as } t_{\text{PHZ}}, t_{\text{PLZ}}.$ 

[4]  $t_t$  is the same as  $t_{THL}$ ,  $t_{TLH}$ .

[5]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu$ W).  $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$  where:  $f_i =$  input frequency in MHz;

 $f_o =$  output frequency in MHz;

 $C_L$  = output load capacitance in pF;

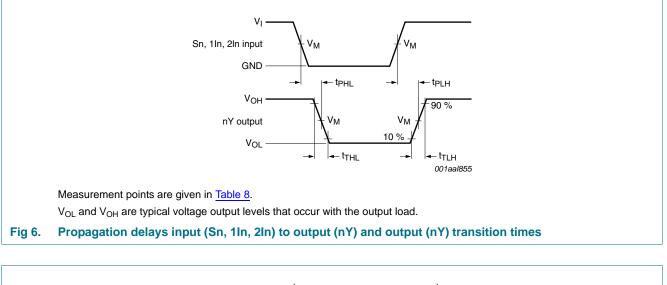
 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of outputs.

Dual 4-input multiplexer; 3-state

# 12. Waveforms



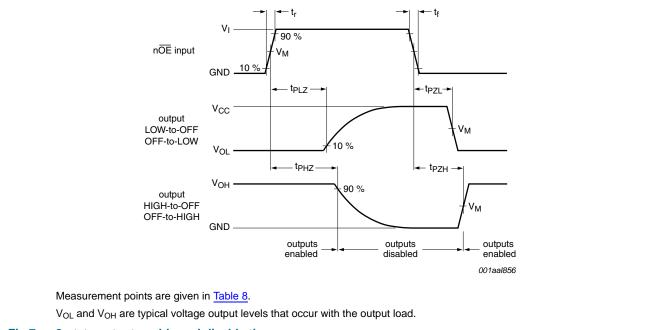


Fig 7. 3-state output enable and disable times

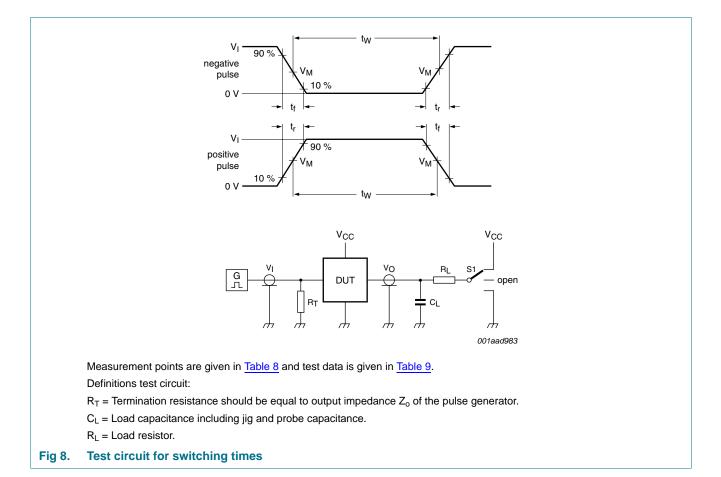
### Table 8.Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74HC253	0.5V <sub>CC</sub>	0.5V <sub>CC</sub>
74HCT253	1.3 V	1.3 V

## **NXP Semiconductors**

# 74HC253; 74HCT253

## Dual 4-input multiplexer; 3-state

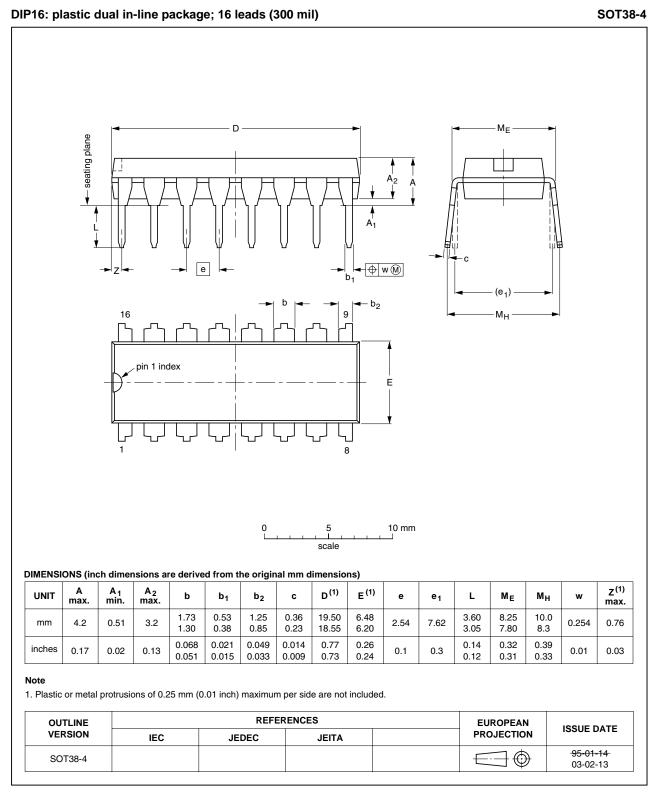


### Table 9. Test data

Туре	Input		Load	Load		Switch position		
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHL</sub> , t <sub>PLH</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
74HC253	V <sub>CC</sub>	6 ns	50 pF	1 kΩ	open	GND	V <sub>CC</sub>	
74HCT253	3 V	6 ns	50 pF	1 kΩ	open	GND	V <sub>CC</sub>	

Dual 4-input multiplexer; 3-state

# 13. Package outline



### Fig 9. Package outline SOT38-4 (DIP16)

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Dual 4-input multiplexer; 3-state

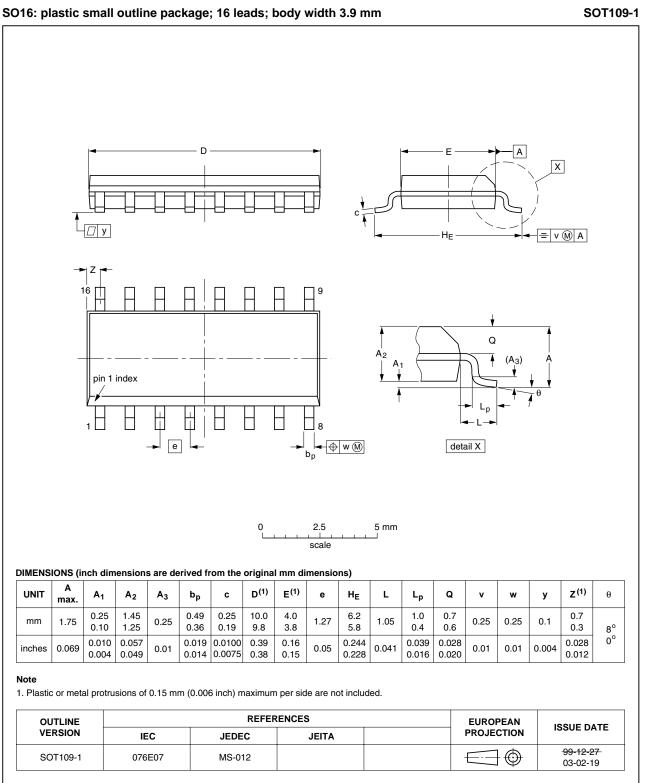


Fig 10. Package outline SOT109-1 (SO16)

Dual 4-input multiplexer; 3-state

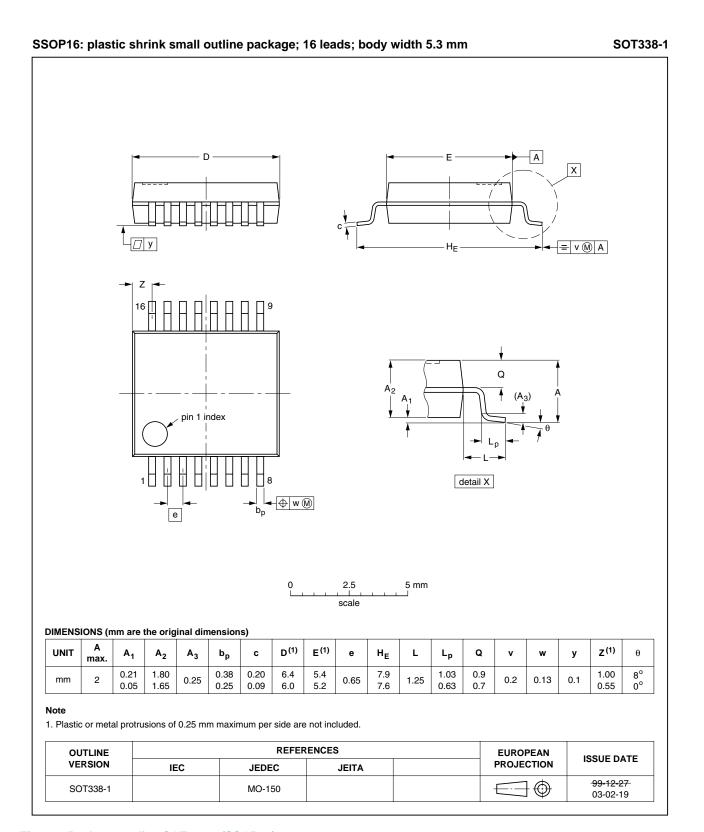


Fig 11. Package outline SOT338-1 (SSOP16)

Dual 4-input multiplexer; 3-state

# 14. Abbreviations

Table 10. Abbreviations				
Acronym	Description			
CMOS	Complementary Metal Oxide Semiconductor			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
MM	Machine Model			
TTL	Transistor-Transistor Logic			

# **15. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74HC_HCT253_3	20100422	Product data sheet	-	74HC_HCT253_CNV_2	
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> </ul>				
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
74HC HCT253 CNV 2	970828	Product specification	-	-	

# **16. Legal information**

## 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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Dual 4-input multiplexer; 3-state

# **17. Contact information**

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